

# **Dual N-Channel 20-V (D-S) MOSFET**

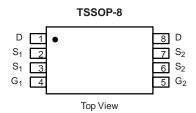
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
20	$0.020$ at $V_{GS} = 4.5 \text{ V}$	4.8		
	$0.032$ at $V_{GS} = 2.5 \text{ V}$	3.5		

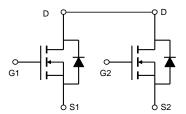
#### **FEATURES**

- Halogen-free Option Available
- TrenchFET® Power MOSFETs









<b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	20		V	
Gate-Source Voltage		$V_{GS}$	± 12			
Continuous Dunin Courset /T 450 °C\2	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	4.8	3.4	٨	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		3.6	2.6		
Pulsed Drain Current		I <sub>DM</sub>	30		Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.5	1.0		
	T <sub>A</sub> = 25 °C	В	1.5	1.0	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	P <sub>D</sub>	0.96	0.64	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Manifester Locality to Assistantia	t ≤ 10 s	R <sub>thJA</sub>	72	83	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	<b>'`</b> thJA	100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	55	70	

- a. Surface Mounted on FR4 board,  $t \le 10 \text{ s.}$
- \* Pb containing terminations are not RoHS compliant, exemptions may apply.

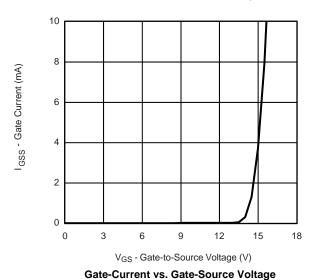


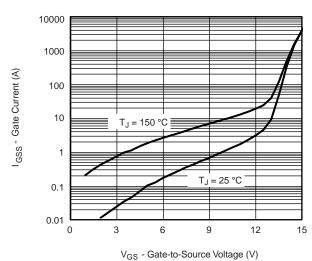
<b>SPECIFICATIONS</b> $T_J = 25$ °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Typ. <sup>a</sup>	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ 0.5		1.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V			1		
		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			25	μA	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
Drain-Source On-State Resistance <sup>b</sup>	В	$V_{GS} = 4.5 \text{ V}, I_D = 6.5 \text{ A}$		0.020		Ω	
	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 5.5 \text{ A}$		0.032			
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6.5 A		30		S	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	I <sub>S</sub> = 1.5 A, V <sub>GS</sub> = 0 V		0.71	1.2	V	
Dynamic <sup>a</sup>							
Total Gate Charge	$Q_g$			12			
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.5 \text{ A}$		2.2		nC	
Gate-Drain Charge	$Q_{gd}$			3.6			
Turn-On Delay Time	t <sub>d(on)</sub>			245	365		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 10 $\Omega$		330	495	no	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 4.5 V, $R_G$ = 6 $\Omega$		860	1300	ns	
Fall Time	t <sub>f</sub>			510	765		

#### Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

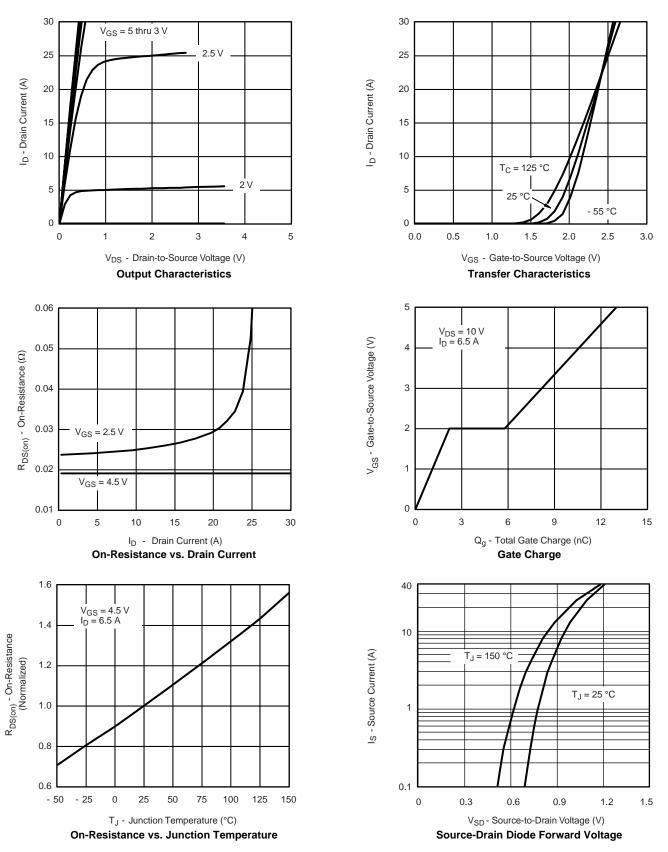
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



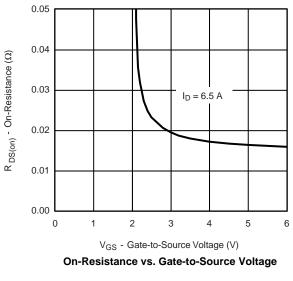


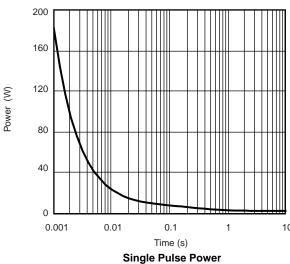
Gate Current vs. Gate-Source Voltage

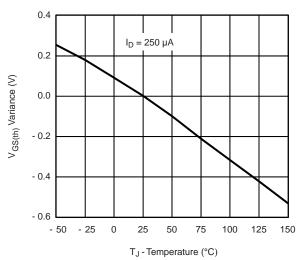




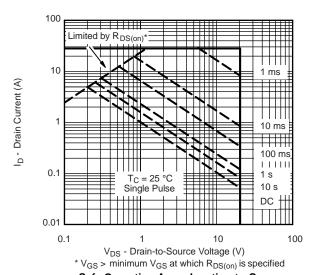




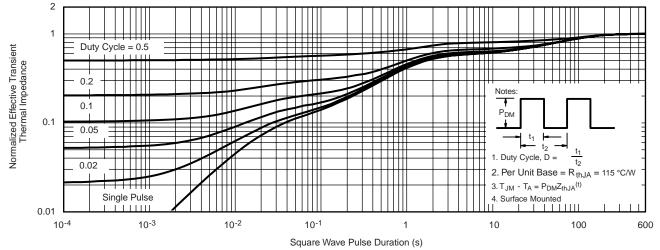




Threshold Voltage

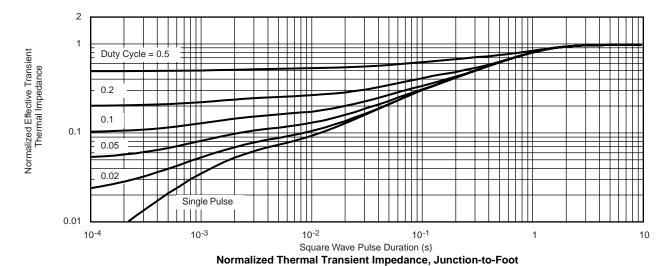


Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient

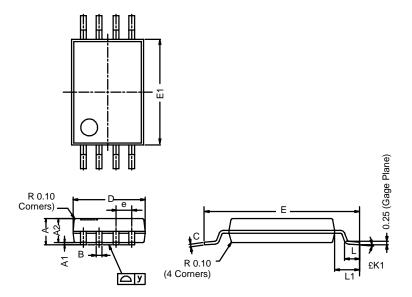






TSSOP: 8-LEAD

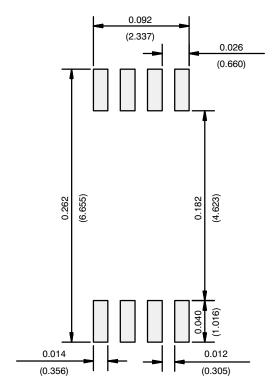
**JEDEC Part Number: MO-153** 



	MILLIMETERS				
Dim	Min	Nom	Max		
Α	-	-	1.20		
A <sub>1</sub>	0.05	0.10	0.15		
A <sub>2</sub>	0.80	1.00	1.05		
В	0.19	0.28	0.30		
С	-	0.127	-		
D	2.90	3.00	3.10		
Е	6.20	6.40	6.60		
E <sub>1</sub>	4.30	4.40	4.50		
е	Ī	0.65	-		
L	0.45	0.60	0.75		
L <sub>1</sub>	0.90	1.00	1.10		
Y	-	_	0.10		
£ <b>K1</b>	0°	3°	6°		
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844					



### **RECOMMENDED MINIMUM PADS FOR TSSOP-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

7



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